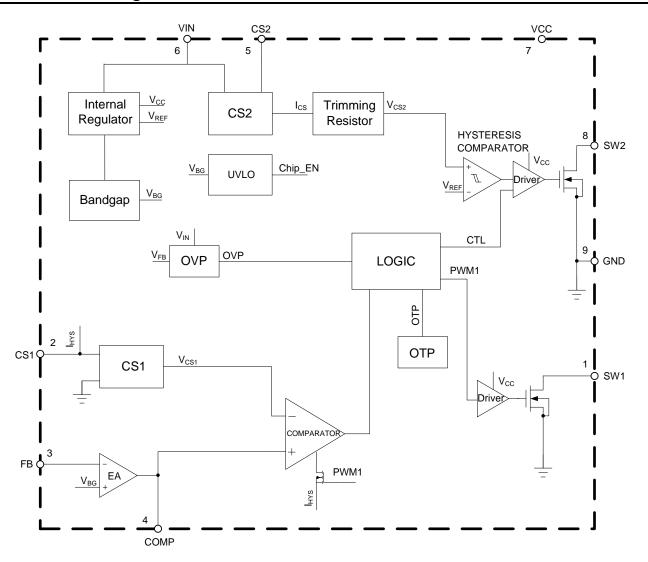


# **Pin Descriptions**

Pin Number	Pin Name	Function
1	SW1	Integrated Boost MOS Drain
2	CS1	Boost Input Current Sense Pin
3	FB	Boost Output Voltage Feedback Pin
4	COMP	Soft-start and Boost Control Loop Compensation
5	CS2	Buck Output Current Sense Pin
6	VIN	IC Input Voltage, Adding from Boost Output Voltage
7	VCC	Supply Voltage For Internal Circuit
8	SW2	Integrated Buck MOS Drain
9	Exposed Pad	Connected To Ground

# **Functional Block Diagram**





# Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified. Note 4)

Parameter	Symbol	Value	Unit
VIN Pin Voltage	V <sub>IN</sub>	-0.3 to 40	V
SW1 Pin Voltage	V <sub>SW1</sub>	-0.3 to 40	V
SW2 Pin Voltage	V <sub>SW2</sub>	-0.3 to 40	V
COMP Pin Voltage	$V_{COMP}$	-0.3 to 6	V
CS1 Pin Voltage	V <sub>CS1</sub>	-0.3 to 6	V
CS2 Pin Voltage	V <sub>CS2</sub>	-0.3 to 40	V
FB Pin Voltage	$V_{FB}$	-0.3 to 6	V
VCC Pin Voltage	Vcc	-0.3 to 6	V
Operating Junction Temperature	$T_J$	+150	°C
Storage Temperature	T <sub>STG</sub>	-65 to +150	°C
Thermal Resistance (Junction To Ambient) (Note 5)	θја	66	°C/W
Lead Temperature (Soldering, 10sec)	$T_LEAD$	+300	°C
ESD (Machine Model)	_	200	V
ESD (Human Body Model)	-	2000	V

Notes:

- 4. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.
- 5. Device mounted on FR-4 PCB (51mm x 51mm) 2oz copper, minimum recommended pad layout on top layer and thermal vias to bottom layer ground plane. For better thermal performance, larger copper pad for heat-sink is needed.

# **Recommended Operating Conditions**

Symbol	Parameter	Min	Max	Unit
V <sub>IN</sub>	VIN Pin Voltage	5	36	٧
T <sub>A</sub>	Ambient Temperature	-40	+105	°C



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

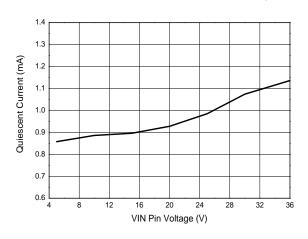
Parameters	Symbol	Conditions	Min	Тур	Max	Unit		
Input Supply								
VIN Pin Voltage	V <sub>IN</sub>	_	5	_	36	V		
Quiescent Current	IQ	No Switching	_	1	_	mA		
Under-Voltage Lockout Voltage	V <sub>UVLO</sub>	V <sub>IN</sub> Rising	_	4.2	_	V		
UVLO Hysteresis	V <sub>HYS</sub>	_	_	500	_	mV		
VCC Regulator		•	<u>.</u>					
VCC Pin Voltage	Vcc	_	4.5	5	5.5	V		
Source Current Capability	_	V <sub>CC</sub> = 5V	10	_	_	mA		
Load Regulation	_	_	_	4	_	%		
Integrated NMOS_BUCK	11	- 1	<b>!</b>			l		
MOS Voltage Stress (Note 6)	V <sub>DS1</sub>	_	_	40	_	V		
MOS Current Stress (Note 6)	I <sub>DS1</sub>	_	_	2	_	Α		
MOS R <sub>DSON</sub>	R <sub>DSON1</sub>	_	_	250	_	mΩ		
Integrated NMOS_BOOST						l		
MOS Voltage Stress (Note 6)	V <sub>DS2</sub>	_	_	40	_	V		
MOS Current Stress (Note 6)	I <sub>DS2</sub>	_	_	2	_	Α		
MOS R <sub>DSON</sub>	R <sub>DSON2</sub>	_	_	250	_	mΩ		
Compensation and Soft Start (COMP Pin)	1	- 1	•			l		
Error Amplifier Trans-conductance	GEA	_	_	1000	_	μΑ/V		
Sourcing Current	I <sub>O_H</sub>	V <sub>COMP</sub> = 0.5V	_	68	_	μA		
Sinking Current	lo_L	V <sub>COMP</sub> = 4.5V	_	68	_	μA		
FB Pin Voltage	$V_{FB}$	_	1.18	1.22	1.26	V		
FB OVP Voltage	V <sub>OVP</sub>	_	1.59	1.66	1.75	V		
FB OVP Voltage Hysteresis	V <sub>OVP_HYS</sub>	_	0.15	0.2	0.25	V		
Hysteresis Competitor (Boost)	11	- 1	<b>.</b>			l		
Boost Sense Voltage Low Level	V <sub>CS1_MIN</sub>	V <sub>COMP</sub> = 0V	_	-90	_	mV		
Hysteresis Current	I <sub>HYS</sub>	_	85	100	115	μΑ		
Hysteresis Competitor (Buck)								
Buck Sense Voltage High Level	V <sub>CSH</sub>	_	_	115	_	mV		
Buck Sense Voltage Low Level	V <sub>CSL</sub>	_	_	85	_	mV		
Buck Sense Voltage Average Level	V <sub>CS2_AVE</sub>	_	95	100	105	mV		
Over-Temperature Protection	1	•	I		ı	ı		
Thermal Shutdown (Note 6)	T <sub>OTSD</sub>	_	+140	+160	_	°C		
	T <sub>HYS</sub>	_	_	+40	_	°C		

Note 6: These parameters, although guaranteed by design, are not 100% tested in production.

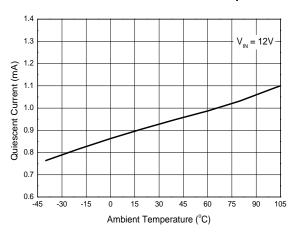


## **Performance Characteristics**

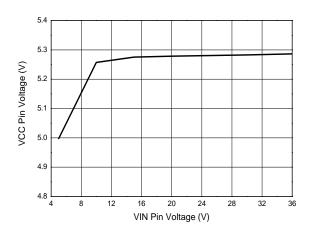
### **Quiescent Current vs. VIN Pin Voltage**



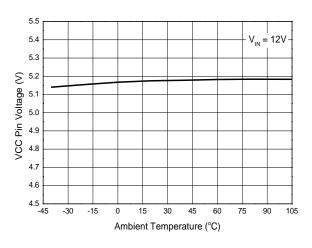
### **Quiescent Current vs. Ambient Temperature**



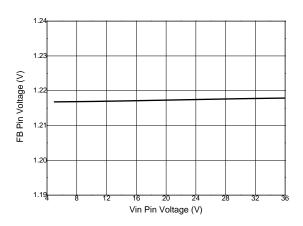
## VCC Pin Voltage vs. VIN Pin Voltage



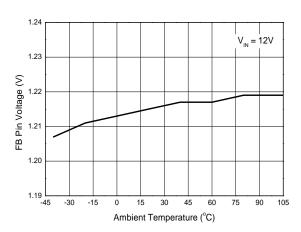
### VCC Pin Voltage vs. Ambient Temperature



## FB Pin Voltage vs.VIN Pin Voltage



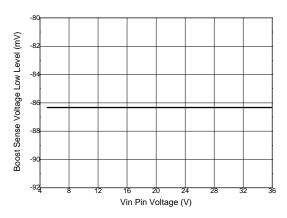
## FB Pin Voltage vs. Ambient Temperature



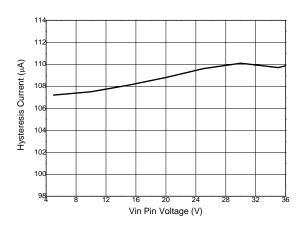


## **Performance Characteristics (Cont.)**

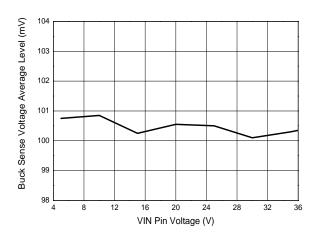
## Boost Sense Voltage Low Level vs. **VIN Pin Voltage**



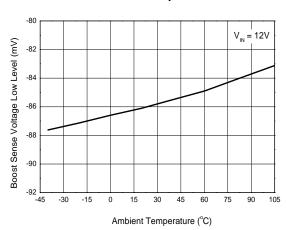
## Hysteresis Current vs. VIN Pin Voltage



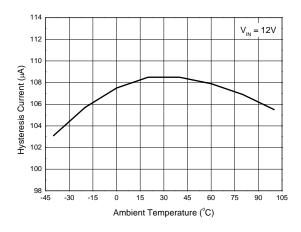
**Buck Sense Voltage Average Level vs. VIN Pin Voltage** 



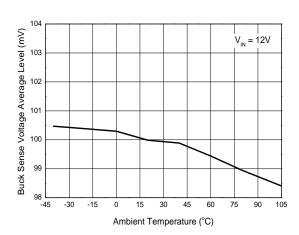
## **Boost Sense Voltage Low Level vs. Ambient Temperature**



Hysteresis Current vs. Ambient Temperature



**Buck Sense Voltage Average Level vs. Ambient Temperature** 





# **Application Information**

#### AL8820 Operation

The device integrates two DC/DC regulators. This two stage design offers superior performance for MR16/AR111 applications. The first stage is a boost PFC stage which improves PF, reduces EMI and conditions the input to be compatible with many of the most commonly used Electronic Transformers (ET). This input stage also provides power for the second stage buck converter which provides regulated constant output current for the LEDs

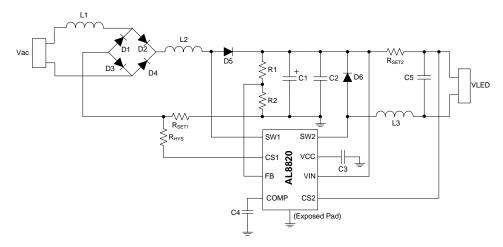


Figure 1. Typical Application Circuit

### V<sub>IN</sub> Voltage Setting

V<sub>IN</sub> Voltage is the output voltage of boost section and is also the input voltage of the buck section. Therefore V<sub>IN</sub> must be set sufficiently higher than the output voltage of buck section. For the Boost application, the output voltage can be defined as:

$$V_{IN} = 1.22V \times \frac{R1 + R2}{R2}$$

#### R<sub>SET1</sub> and R<sub>HYS</sub> Setting

The Boost converter of the AL8820 operates at continuous conduction mode and is based on hysteresis schematic which has lower threshold and upper threshold. Refer to Figure 2 depicting the inductor current waveform.

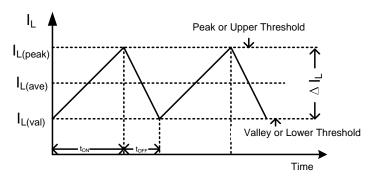


Figure 2. Inductor Current

When switch SW1 is turned on, the inductor current flows through  $R_{SET1}$  and ramps up linearly. The rising current produces a voltage ramp across  $R_{SET1}$ . When the voltage across  $R_{SET1}$  reaches the upper threshold, switch SW1 is turned off. The inductor current continues to flow through  $R_{SET1}$  but decays. The decaying current produces a falling voltage at  $R_{SET1}$ . When the voltage across  $R_{SET1}$  falls to the lower threshold, switch SW1 is turned on again.

The lower threshold voltage  $V_{LT}$  depends on the voltage  $V_{COMP}$  at COMP pin that varies with the input voltage and output load. The equation is shown as below.



$$V_{LT} = \begin{cases} \frac{(V_{COMP} - 1.5) \times 0.6 + 1.4}{16} mV, 1.5V \le V_{COMP} \le 5V \\ 88mV, 0V \le V_{COMP} \le 1.5V \end{cases}$$

The range of  $V_{COMP}$  is from 0V to 5V.

The upper threshold depends on the lower threshold and the hysteresis value. The hysteresis value is set by external resister R<sub>HYS</sub>. It is defined as below.

$$V_{HYS} = R_{HYS} \times 100 \mu A$$

According to the operation principle , the peak to peak current  $\Delta I_L$  and the valley current  $I_{L(val)}$  can be obtained by the below equations.

$$I_{L(val)} = \frac{V_{LT}}{R_{SET1}}$$

$$\Delta I_L = \frac{V_{HYS}}{R_{SET1}}$$

Where:

 $\Delta I_L$  is the peak to peak current of inductor.

 $I_{L(val)}$  is the valley current of inductor.

From the Figure 2, the relationship between  $I_{L(peak)}$ ,  $I_{L(val)}$ ,  $I_{L(ave)}$  and  $\Delta I_{L}$  can be obtained as below.

$$I_{L(peak)} = I_{L(val)} + \Delta I_{L}$$

$$I_{L(ave)} = I_{L(val)} + \frac{1}{2} \times \Delta I_{L}$$

Where:

I<sub>L(peak)</sub> is the peak current of inductor.

I<sub>L(ave)</sub> is the average current of inductor.

As we know the average current  $I_{L(ave)}$  depends on the output power, rated input voltage  $V_{IN1}$  of boost converter and total efficiency  $\eta$ . So the average current  $I_{L(ave)}$  can be obtained by the below equation.

$$I_{L(ave)} = \frac{V_{LED} \times I_{LED}}{\eta \times V_{IN1}}$$

Where:



V<sub>LED</sub> is the output voltage of Buck converter.

I<sub>LED</sub> is the output current of Buck converter.

Set ratio of  $\Delta I_L$  to  $I_{L(peak)}$  as K.

$$K = \frac{\Delta I_L}{I_{L(peak)}}$$

R<sub>SET1</sub> and R<sub>HYS</sub> can be obtained from above equations:

$$R_{SET1} \! = \! \begin{cases} \frac{((V_{COMP} - 1.5) \times 0.6 + 1.4) \times (2 - K) \times \eta \times V_{IN1} \times 10^{-3}}{32 \times V_{LED} \times I_{LED} \times (1 \! - \! K)} 1.5V \leq V_{COMP} \leq 5V \\ \frac{44 \times (2 - K) \times \eta \times V_{IN1} \times 10^{-3}}{V_{LED} \times I_{LED} \times (1 \! - \! K)}, 0V \leq V_{COMP} \leq 1.5V \end{cases}$$

$$R_{HYS} = \frac{2 \times V_{LED} \times I_{LED} \times K \times R_{SET1} \times 10^4}{\eta \times V_{IN1} \times (2 - K)}$$

When the value of K,  $\eta$  and V<sub>COMP</sub> are provided, the value of resister R<sub>SET1</sub> and R<sub>HYS</sub> can be calculated according to these above equations. In order to get appropriate efficiency and Electronic Transformer (ET) compatibility, generally K is set between 0.4 and 0.8. Due to the range of V<sub>COMP</sub> is from 0V to 5V, in order to get output voltage regulation, generally V<sub>COMP</sub> is set as 3V at rated input voltage.

#### **Step-Up Converter Inductor Selection**

Because of the using of the hysteretic control scheme, the switching frequency in a boost configuration can be adjusted in accordance to the value of the inductor being used. The value of the inductor can be determined by using the following equation:

$$L2 = \frac{[V_{IN1} - (R_{SET1} + R_L + R_{DSON1}) \times I_{L(ave)}] \times [V_{IN} - V_{IN1} - V_F - (R_L + R_{SET1}) \times I_{L(ave)}]}{\Delta I_L[V_{IN} - V_F - (2R_{SET1} + 2R_L - R_{DSON1}) \times I_{L(ave)}] \times f_{SW1}}$$

Where:

L2 is the coil inductance.

R<sub>L</sub> is the coil resistance.

 $R_{\text{SET1}}$  is the current sense resistance.

R<sub>DSON1</sub> is the switch SW1 resistance.

V<sub>IN1</sub> is the rated input voltage of the boost converter.

V<sub>IN</sub> is the output voltage of boost converter.

V<sub>F</sub> is the diode forward voltage at the required load current.

 $f_{\text{SW1}}$  is the desired switching frequency.



Low switching frequency can decrease the switching loss but need to choose higher inductor values that will result in larger size in order to meet the saturation current. For example, the relationship between switching frequency and inductor value is shown as below Table 1 in the same application system. Considering these factors, 500kHz switching frequency is recommended in typical application.

Inductance Value of L2 @ Vac = 12Vac, $V_{IN}$ = 22V, $V_{OUT}$ = 10V, $I_{OUT}$ = 650mA	Operation Frequency of SW1 at Peak Voltage of Vac
10µH	637kHz
15µH	500kHz
27µН	373kHz

Table 1

### **LED Current Control**

The LED current is controlled by the resistor R<sub>SET2</sub> in Figure 1.

Connected between VIN pin and CS2 pin, the nominal average output current in the LED(s) is defined as:

$$I_{LED} = \frac{100mV}{R_{SET2}}$$

#### **Buck Converter Inductor Selection**

The inductance L3 in Buck converter is determined by the following factors: inductor ripple current, switching frequency,  $V_{LED}/V_{IN}$  ratio, internal FET, and component parameter. The inductance L3 is calculated according to the following equation:

$$L3 \geq \frac{V_{\mathit{IN}} - V_{\mathit{LED}} - (R_{\mathit{SET2}} + R_{\mathit{DSON2}} + R_{\mathit{COIL}}) \times I_{\mathit{LED}}}{\Delta I_{\mathit{LED}}} \times \frac{V_{\mathit{LED}}}{V_{\mathit{IN}}} \times \frac{1}{f_{\mathit{SW2}}}$$

Where:

V<sub>IN</sub> is the output voltage of Boost converter.

V<sub>LED</sub> is the output voltage of Buck converter.

R<sub>SET2</sub> is the current sense resistance.

 $R_{DSON2}$  is the switch resistance (=0.25 $\Omega$ ).

 $R_{\text{COIL}}$  is the coil resistance of inductor L3.

 $\Delta I_{LED}$  is the coil peak-peak ripple current, internally set to 0.25 x  $I_{LED}$ .

f<sub>SW2</sub> is the switching frequency.

The low switching frequency  $f_{SW2}$  is recommended in order to minimize errors due to switching delays which will result in increased ripple and lower efficiency. Higher switching frequency can choose smaller inductor value that has smaller size in order to meet the saturation current but will increase the switching loss. For example, the relationship between switching frequency and inductor value is shown as below Table 2 in the same application system. Considering these factors, about 300kHz switching frequency is recommended in typical application.



Inductance Value of L3 @ V <sub>IN</sub> = 22Vac, V <sub>OUT</sub> = 10V, I <sub>OUT</sub> = 650mA	Operation Frequency of SW2
33µН	756kHz
47μH	568kHz
68µН	397kHz
100µH	257kHz

Table 2

#### **VIN OVP Protection**

The AL8820 has two kinds of Over-voltage (OVP) protection both of which turn off the power switch SW1. When the voltage at the FB pin exceeds threshold approximately 1.66V, the power switch of step-up stage is turned off. The power switch of boost section can be turned on again once the voltage at the FB pin drops below 1.46V.

The AL8820 additionally has an internal over voltage protection to protect the AL8820 from excessive input voltage. When the voltage applied at VIN pin exceeds 39V, it will turn off the power switch SW1. The power switch will turn on once the voltage at  $V_{IN}$  drops below 34V.

#### **VCC** Regulator

The VCC pin requires a capacitor for stable operation and to store the charge for the large GATE switching currents. Choose a 10V rated low ESR, X7R or X5R, ceramic capacitor for best performance. A 4.7µF capacitor will be adequate for many applications. Place the capacitor close to the IC to minimize the trace length between the VCC pin and the exposed pad.

An internal current limit on the VCC output protects against excessive on-chip power dissipation. The VCC pin has set the output to 5V (typ.) to protect the internal FETs from excessive power dissipation caused by not being fully enhanced. If the VCC pin is used to drive extra circuits beside the AL8820, the extra loads should be limited to less than 8mA.

### **Output Capacitor C1 and C2 of Boost**

The capacitor C1 is used to hold the bus voltage when the electronic transformer has no output. For most applications, it is recommended to use an aluminum electrolytic capacitor with greater than 220µF capacitance.

The output capacitor C2 is selected to handle the output ripple noise requirements. For the best performance, it is recommended to use X7R or better grade ceramic capacitor greater than  $1\mu F$  capacitance.

#### **Compensation Capacitor C4**

In applications powered by electronic transformer, the input voltage can change roughly in one cycle of AC power frequency. A 1µF ceramic capacitor C4 connected from COMP pin to ground help to stabilize the control loop of the Boost regulator.

### **Output Capacitor C5 of Buck**

Higher LED current ripple will shorten the LED life time and increase heat accumulation of LED. To reduce the LED current ripple, an output capacitor in parallel with the LED should be added. Lower ripple can be achieved with higher capacitor values. For most applications, a value of  $4.7\mu$ F is recommended.

#### **Diode Selection**

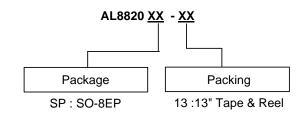
For maximum efficiency and performance, the rectifiers (D5, D6) should be fast low capacitance Schottky diodes with low reverse leakage at maximum operating voltage and temperature. With its low power dissipation, the Schottky diode outperforms other silicon diodes and increases overall efficiency.

#### **Over Temperature Protection**

A over temperature protection feature is to protect the AL8820 from excessive internal temperature. When the junction temperature exceeds +160°C, the internal FETs will be turned off. When junction temperature drops below +120°C, IC will turn on both FETs and return to normal operation.

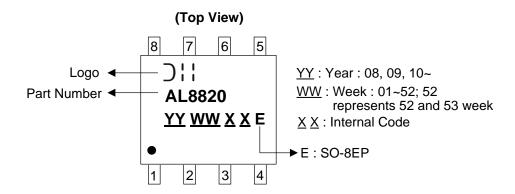


# **Ordering Information**



Part Number	Package Code	Doolsono	13" Tape and Reel		
		Package	Quantity	Part Number Suffix	
AL8820SP-13	SP	SO-8EP	2500/Tape & Reel	-13	

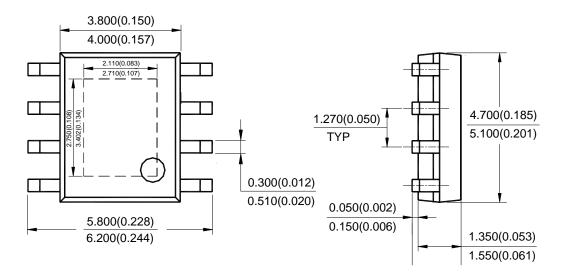
# **Marking Information**

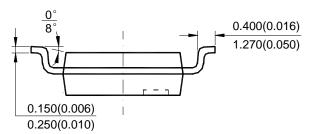




# Package Outline Dimensions (All dimensions in mm(inch).)

## (1) Package Type: SO-8EP



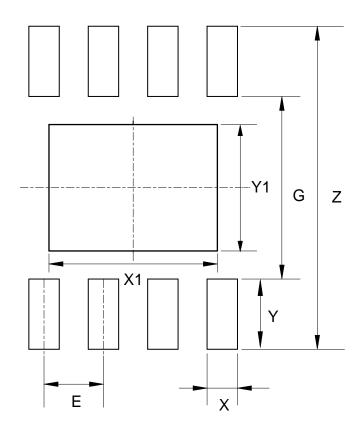


Note: Eject hole, oriented hole and mold mark is optional.



# **Suggested Pad Layout**

(1) Package Type: SO-8EP



Dimensions	Z	G	Х	Υ	X1	Y1	E
Dimensions	(mm)/(inch)						
Value	6.900/0.272	3.900/0.154	0.650/0.026	1.500/0.059	3.600/0.142	2.700/0.106	1.270/0.050



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